S71PL-N MirrorBit® MCPs

S71PL256N, S71PL127N, S71PL129N 256/128/128 Megabit (16/8/8 M x 16-Bit) CMOS 3.0 Volt-only Simultaneous Read/Write, Page Mode Flash Memory



Data Sheet

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Full Production (No Designation on Document)

When a product has been in production for a period of time such that no changes or only nominal changes are expected, the Preliminary designation is removed from the data sheet. Nominal changes may include those affecting the number of ordering part numbers available, such as the addition or deletion of a speed option, temperature range, package type, or V_{IO} range. Changes may also include those needed to clarify a description or to correct a typographical error or incorrect specification. Spansion Inc. applies the following conditions to documents in this category:

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Data Sheet

Features

- Speed
 - Flash: 70 ns - pSRAM: 70 ns
- 8.0 x 11.6 x 1.2 mm Packages
 - 84-Ball Fine-Pitch Ball Grid Array (FBGA) S71PL256NC0 S71PL256ND0
 - 64 Ball Fine-Pitch Ball Grid Array (FBGA) S71PL129NB0

S71PL129NC0 S71PL127NB0 S71PL127NC0

- - Flash: 70 ns
 - pSRAM: 70 ns
- Operating Temperature Range
 - Temperature Range of -25°C to +85°C

General Description

This document contains information for the S71PL-N MirrorBit MCP product. For detailed specifications, please refer to the individual data sheets:

| Document | Publication Identification Number (PID) |
|---------------------------|---|
| S29PL-N | S29PL-N_00 |
| 32M pSRAM Type 8 (90 nm) | comspec_02 |
| 32M pSRAM Type 8 (130 nm) | pSRAM_31 |
| 32M pSRAM Type 7 | pSRAM_29 |
| 32M pSRAM Type 2 | pSRAM_19 |
| 64M pSRAM Type 2 | pSRAM_20 |
| 64M pSRAM Type 8 (90 nm) | SPH064D970R1R |
| 64M pSRAM Type 8 (130 nm) | pSRAM_32 |
| 128M pSRAM Type 2 | pSRAM_15 |



1. Flash/RAM Combinations Table

| | | | pSRAM Density | |
|---------------|--------|-------------|---------------|-------------|
| | | 32 Mb | 64 Mb | 128 Mb |
| | PL127N | S71PL127NB0 | S71PL127NC0 | |
| Flash Density | PL129N | S71PL129NB0 | S71PL129NC0 | |
| | PL256N | | S71PL256NC0 | S71PL256ND0 |

2. Product Selector Guide

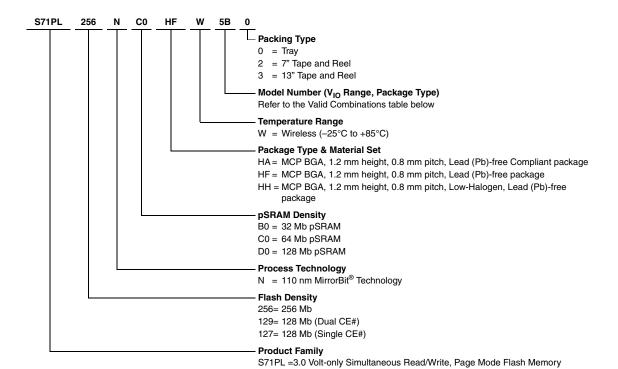
| Device | pSRAM Density | pSRAM Type |
|-------------|---------------|----------------------------|
| S71PL127NB0 | 32 Mb | pSRAM Type 2 |
| S71PL127NB0 | 32 Mb | pSRAM Type 7 |
| S71PL127NB0 | 32 Mb | pSRAM Type 8 (90 & 130 nm) |
| S71PL127NC0 | 64 Mb | pSRAM Type 2 |
| S71PL127NC0 | 64 Mb | pSRAM Type 8 (90 & 130 nm) |
| S71PL129NB0 | 32 Mb | pSRAM Type 2 |
| S71PL129NB0 | 32 Mb | pSRAM Type 7 |
| S71PL129NB0 | 32 Mb | pSRAM Type 8 (130 nm) |
| S71PL129NC0 | 64 Mb | pSRAM Type 2 |
| S71PL129NC0 | 64 Mb | pSRAM Type 8 (90 & 130 nm) |
| S71PL256NC0 | 64 Mb | pSRAM Type 2 |
| S71PL256NC0 | 64 Mb | pSRAM Type 8 (90 & 130 nm) |
| S71PL256ND0 | 128 Mb | pSRAM Type 2 |

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3. Ordering Information

The order number is formed by a valid combinations of the following:





3.1 Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult your local sales office to confirm availability of specific valid combinations and to check on newly released combinations.

Table 3.1 Valid Combinations

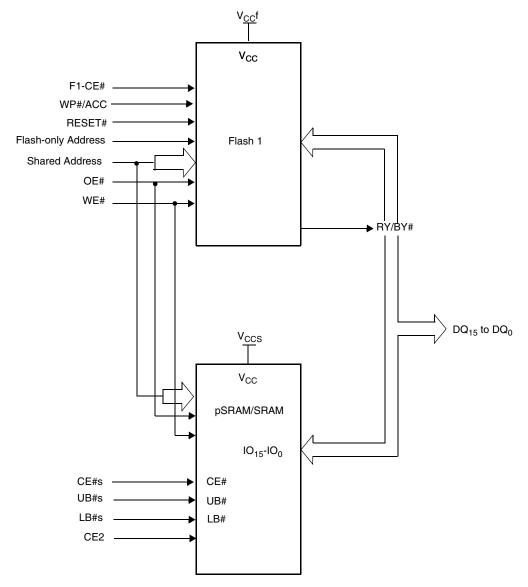
| Base Ordering Part Number (2) | Package & Temperature | Model Number | Packing Type | pSRAM Type | Flash Speed Option | pSRAM Speed Options | Package Name | | |
|----------------------------------|--------------------------|-----------------|---------------------|---------------|--------------------------|----------------------------|-------------------------------|-------------------------------------|----------|
| | | 4B (4) | | Type 2 | | | | | |
| S71PL127NB0 | HAW, HFW | 4U | | Type 8 | | | | | |
| 3/1FL12/NB0 | | 4Z (4) | | Type 7 | | | | | |
| | HHW | 4U | | Type 8 | | | | | |
| 074514071100 | | 4B (4) | | | | Type 2 | | | TLA064 - |
| S71PL127NC0 | | 4U | | Type 8 (5) | | | 8 x 11.6 x 1.2 mm, 64-ball | | |
| | | 4B (4) | 0.00 | Type 2 | | | | | |
| S71PL129NB0 | '1PL129NB0 | 4U (4) | 0, 2, 3 (1), (2) | Type 8 | 70 ns | 70 ns | | | |
| | | 4Z (4) | | Type 7 | | | | | |
| S71PL129NC0 | HAW, HFW | 5B (4) | | Type 2 | | | | | |
| 37 IPL129NC0 | | | | Type 8 (5) | | | | | |
| S71PL256NC0 | | | Type 2 | | | TLA084- | | | |
| 3/1FL256NC0 | | | Type 8 (5) | | | 8 x 11.6 x 1.2 mm, 84-ball | | | |
| S71PL256ND0 | | 5B (4) | | | Type 2 | | | TSB084 - 8 x 11.6 x 1.2, 84-ball | |

Notes:

- 1. Type 0 is standard. Specify other options as required.
- 2. BGA package marking omits leading "S" and packing type designator from ordering part number.
- 3. Contact factory for availability for any of the OPNs listed since RAM type availability may vary over time.
- 4. Part not recommended for new designs.
- 5. MCP with 90 nm Type 8 pSRAM has package material character F for Pb-free but also satisfies low-Halogen requirement.



4. Block Diagram



Notes:

- 1. RY/BY# is an open drain output.
- 2. $A_{MAX} = A23 \; (PL256N), \; A22 \; (PL127N), \; A21 \; (PL129N).$



5. Physical Dimensions/Connection Diagrams

This section shows the I/O designations and package specifications for the S71PL-N.

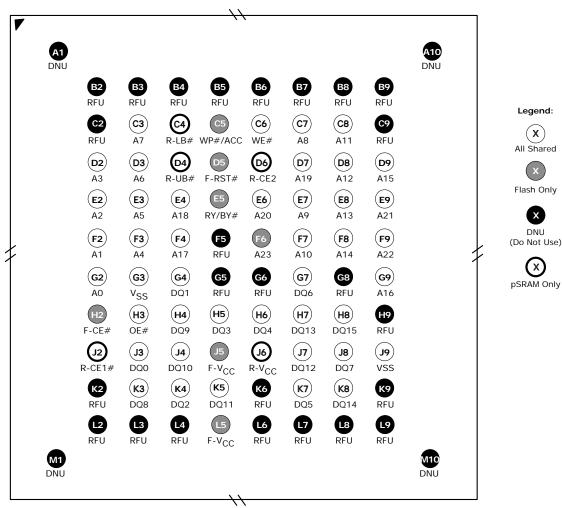
5.1 Special Handling Instructions for FBGA Package

Special handling is required for Flash Memory products in FBGA packages.

Flash memory devices in FBGA packages may be damaged if exposed to ultrasonic cleaning methods. The package and/or data integrity may be compromised if the package body is exposed to temperatures above 150°C for prolonged periods of time.

5.2 S71PL256N TLA084/TSB084

Figure 5.1 84-ball Fine-Pitch Ball Grid Array (S71PL256N)



Note:

6

Top view—balls facing down.

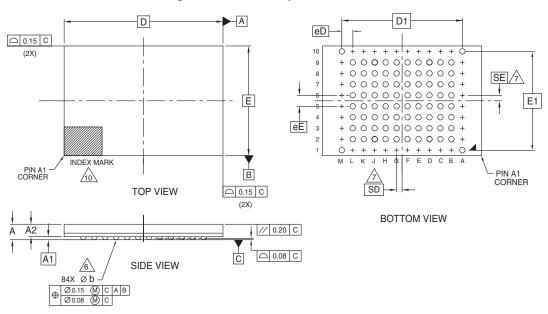
The addresses that are shared vary by MCP combination as shown in the table below:

| | Flash-only Addresses | Shared Addresses |
|-------------|----------------------|------------------|
| S71PL256NC0 | A23-A22 | A21:A0 |
| S71PL256ND0 | A23 | A22:A0 |

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Figure 5.2 TSB084 Physical Dimensions



| PACKAGE | | TSB 084 | | |
|---------|---|-------------------------|----------------------------|--------------------------|
| JEDEC | N/A | | | |
| DxE | 11.6 | 60 mm x 8.00 PACKAGE | mm | |
| SYMBOL | MIN | NOM | MAX | NOTE |
| Α | | | 1.20 | PROFILE |
| A1 | 0.17 | | | BALL HEIGHT |
| A2 | 0.81 | | 0.97 | BODY THICKNESS |
| D | | 11.60 BSC. | | BODY SIZE |
| E | | 8.00 BSC. | | BODY SIZE |
| D1 | 8.80 BSC. | | | MATRIX FOOTPRINT |
| E1 | 7.20 BSC. | | | MATRIX FOOTPRINT |
| MD | 12 | | | MATRIX SIZE D DIRECTION |
| ME | | 10 | | MATRIX SIZE E DIRECTION |
| n | | 84 | | BALL COUNT |
| φb | 0.35 | 0.40 | 0.45 | BALL DIAMETER |
| eЕ | 0.80 BSC | | | BALL PITCH |
| eD | 0.80 BSC | | | BALL PITCH |
| SD / SE | 0.40 BSC | | | SOLDER BALL PLACEMENT |
| | A2,A3,A4,A5,A6,A7,A8,A9 B1,B10,C1,C10,D1,D10 E1,E10,F1,F10,G1,G10 H1,H10,J1,J10,K1,K10,L1,L10 M2,M3,M4,M5,M6,M7,M8,M9 | | 1,D10 1,G10 0,L1,L10 | DEPOPULATED SOLDER BALLS |

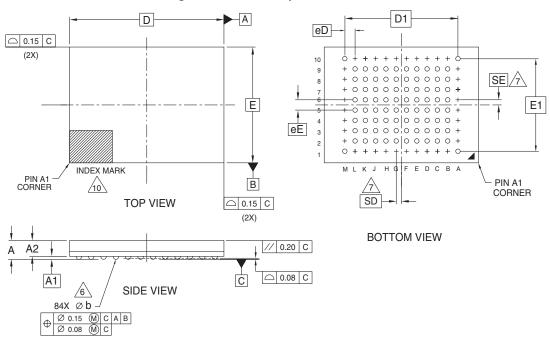
NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
- e REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
 - SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
 - n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- 6 DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL
- DIAMETER IN A PLANE PARALLEL TO DATUM C. ₹ SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
 - WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.
 - WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = e/2
- "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS
- N/A
- 10 A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

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Figure 5.3 TLA084 Physical Dimensions



| PACKAGE | | TLA 084 | | |
|---------|--|-------------------------|------|--------------------------|
| JEDEC | N/A | | | |
| DxE | 11.6 | 60 mm x 8.00 PACKAGE | mm | |
| SYMBOL | MIN | NOM | MAX | NOTE |
| Α | | | 1.20 | PROFILE |
| A1 | 0.17 | | | BALL HEIGHT |
| A2 | 0.81 | | 0.97 | BODY THICKNESS |
| D | | 11.60 BSC. | | BODY SIZE |
| Е | | 8.00 BSC. | | BODY SIZE |
| D1 | | 8.80 BSC. | | MATRIX FOOTPRINT |
| E1 | 7.20 BSC. | | | MATRIX FOOTPRINT |
| MD | 12 | | | MATRIX SIZE D DIRECTION |
| ME | 10 | | | MATRIX SIZE E DIRECTION |
| n | 84 | | | BALL COUNT |
| Øb | 0.35 | 0.40 | 0.45 | BALL DIAMETER |
| eE | | 0:80 BSC. | | BALL PITCH |
| eD | 0.80 BSC | | | BALL PITCH |
| SD/SE | 0.40 BSC. | | | SOLDER BALL PLACEMENT |
| | A2,A3,A4,A5,A6,A7,A8,A9 B1,B10,C1,C10,D1,D10, E1,E10,F1,F10,G1,G10, H1,H10,J1,J10,K1,K10,L1,L10, M2,M3,M4,M5,M6,M7,M8,M9 | | | DEPOPULATED SOLDER BALLS |

NOTES:

- 1. DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- 3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
- 4. e REPRESENTS THE SOLDER BALL GRID PITCH.
- SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

n IS THE NUMBER OF POPULTED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.



6 DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.



SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.

WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = $\boxed{\rm e/2}$

- "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.

10 A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

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5.3 S71PL127N—TLA064

A10 DNU Legend D5 D7 D8 E4 E5 E6 E7 E8 F8 pSRAM Only G8 Do Not Use/ Н8 Reserved for Future Use J8 J4 J5 J7 R-V_{CC} K5 К6 K7 K8 M10 DNU

Figure 5.4 64-ball Fine-Pitch Ball Grid Array (S71PL127N)

Note:

Top view—balls facing down.

The addresses that are shared vary by MCP combination as shown in the table below:

| | Flash-only Addresses | Shared Addresses |
|-------------|----------------------|------------------|
| S71PL127NB0 | A22-A21 | A20:A0 |
| S71PL127NC0 | A22 | A21:A0 |



5.4 S71PL129N—TLA064

DNU С6 Legend D5 Shared E4 E5 E6 E8 pSRAM Only G8 G9 Do Not Use/ Н6 Н7 Н8 Reserved for Future Use J8 K5 M10 DNU

Figure 5.5 64-ball Fine-Pitch Ball Grid Array (S71PL129N)

Note:

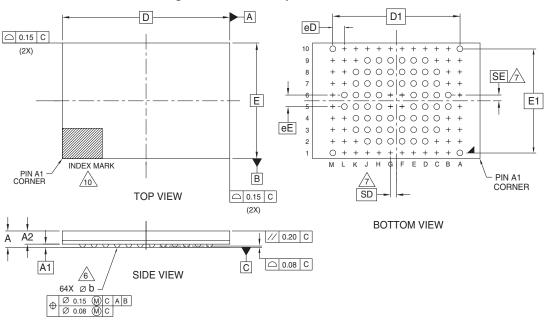
Top view—balls facing down.

The addresses that are shared vary by MCP combination as shown in the table below:

| | Flash-only Addresses | Shared Addresses |
|-------------|----------------------|------------------|
| S71PL129NB0 | A21 | A20:A0 |
| S71PL129NC0 | _ | A21:A0 |



Figure 5.6 TLA064 Physical Dimensions



| PACKAGE | TLA 064 | | | |
|---------|--|------------|--|--------------------------|
| JEDEC | N/A | | | |
| DxE | 11.60 mm x 8.00 mm PACKAGE | | mm | |
| SYMBOL | MIN | NOM | MAX | NOTE |
| Α | | | 1.20 | PROFILE |
| A1 | 0.17 | | | BALL HEIGHT |
| A2 | 0.81 | | 0.97 | BODY THICKNESS |
| D | | 11.60 BSC. | | BODY SIZE |
| Е | | 8.00 BSC. | | BODY SIZE |
| D1 | | 8.80 BSC. | | MATRIX FOOTPRINT |
| E1 | 7.20 BSC. | | | MATRIX FOOTPRINT |
| MD | 12 | | | MATRIX SIZE D DIRECTION |
| ME | 10 | | | MATRIX SIZE E DIRECTION |
| n | | 64 | | BALL COUNT |
| φb | 0.35 | 0.40 | 0.45 | BALL DIAMETER |
| eЕ | | 0:80 BSC. | | BALL PITCH |
| eD | 0.80 BSC | | | BALL PITCH |
| SD / SE | 0.40 BSC. | | | SOLDER BALL PLACEMENT |
| | A2,A3,A4,A5,A6,A7,A8,A9 B1,B2,B3,B4,B7,B8,B9,B10 C1,C2,C9,C10,D1,D10,E1,E10, F1,F5,F6,F10,G1,G5,G6,G10 H1,H10,J1,J10,K1,K2,K9,K10 L1,L2,L3,L4,L7,L8,L9,L10 M2,M3,M4,M5,M6,M7,M8,M9 | | B9,B10 0,E1,E10, ,G6,G10 2,K9,K10 L9,L10 | DEPOPULATED SOLDER BALLS |

NOTES:

- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- 3. BALL POSITION DESIGNATION PER JESD 95-1, SPP-010.
- 4. e REPRESENTS THE SOLDER BALL GRID PITCH.
- 5. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.

SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.

 $\ensuremath{\text{n}}$ is the number of populted solder ball positions for matrix size MD x ME.

6 DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.

SD AND SE ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER

BALL IN THE OUTER ROW.

WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW SD OR SE = 0.000.

WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, SD OR SE = $\left[\text{e/2} \right]$

- 8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
- 9. N/A
- 1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK, METALLIZED MARK INDENTATION OR OTHER MEANS.

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6. Revision History

| Section | Description | |
|--|---|--|
| Revision A (March 11, 2005) | | |
| | Initial release | |
| Revision A1 (April 27, 2005) | | |
| Performance Characteristics pSRAM Density table | Added 128 Mb pSRAM device | |
| Ordering Information and Valid Combination tables | Updated options to include 128 Mb pSRAM device | |
| Block Diagram | Changed chip enable pin from CE#f1 to F1-CE# | |
| Physcial Dimensions/Connection Diagrams | Replaced VBH084 with TLA084 and VSA084 Replaced VBU056 with TLC056 | |
| V _{CC} Power Up | Changed t _{VCS} speed from 30 µs to 50 µs | |
| DC Characteristics | Changed I _{CC4} Max. to 50 μA | |
| Revision A2 (August 18, 2005) | | |
| Global | Removed all references to 56-ball package | |
| Performance Characteristis | Updated the product selector tables | |
| Ordering Information | Updated model number | |
| Valid Combinations table | Added new ordering options | |
| Occupation Biography | Updated the PL127N connection diagram | |
| Connection Diagram | Updated the PL12xN connection diagram | |
| Revision A3 (October 21, 2005) | | |
| Performance Characteristics | Updated the Typical Sector Erase times | |
| Revision A4 (November 29, 2005) | | |
| Global | Added the 1.2 mm option to S71PL256ND0 | |
| Global | Updated the S29PL-N Flash data sheet | |
| Revision A5 (January 3, 2006) | | |
| | Changed the name of in F3 from A14 to A4 in pinout figure of section 3.2 | |
| | Removed all references to Type 6 pSRAMs from the Product Selector Guide | |
| Global | Added a document reference table | |
| | Modified the Package Type and Material options | |
| | Removed the VSA084 package option Removed the datasheet from the MCP wrapper | |
| Devicion AC (April 12, 2006) | Removed the datasneet from the MCP wrapper | |
| Revision A6 (April 12, 2006) | Added a CDAM Time 7 on an entire to C71 DI 107ND0 and C71 DI 100ND0 | |
| Global | Added pSRAM Type 7 as an option to S71PL127NB0 and S71PL129NB0 | |
| Revision A7 (September 6, 2006) | Hadeted degrapest to new templete | |
| Global | Updated document to new template. | |
| Revision A8 (October 6, 2006) | Added 20 Mb vCDAM Time 0 to the valid combinations | |
| Global | Added 32 Mb pSRAM Type 8 to the valid combinations | |
| Revision A9 (December 8, 2006) | Added 64 Mb nCDAM Time 8 to the valid combinations | |
| Global | Added 64 Mb pSRAM Type 8 to the valid combinations. | |
| Revision A10 (June 27, 2008) | Added ODN C71DI 107ND0I I INVIII | |
| Global Consert Description | Added OPN S71PL127NB0HHW4U | |
| General Description | Added 32M pSRAM Type 8 (90 nm) | |
| Ordering Information | Added Package Type & Material Set ordering option HH | |
| Valid Combinations | Added Note 4 for parts with pSRAM Type 2 or 7 | |



| Section | Description | | |
|-----------------------------|---|--|--|
| Revision A11 (June 9, 2010) | | | |
| | Corrected 32 Mb pSRAM Type 8 (90 nm) PID to comspec_02 | | |
| General Description | Clarified that PID pSRAM_32 is for 64 Mb pSRAM Type 8 (130 nm) | | |
| | Added PID SPH064D970R1R for 64 Mb pSRAM Type 8 (90 nm) | | |
| Product Selector Guide | Clarified that pSRAM Type 8 may be of either 90 nm or 130 nm node for both 32 and 64 Mb | | |
| Valid Combinations | Added Note 5 for MCPs with pSRAM Type 8 (90 nm) | | |
| Valid Combinations | Added Note 4 to all PL129N and PL256N MCP combinations | | |

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